



UNISONIC TECHNOLOGIES CO., LTD

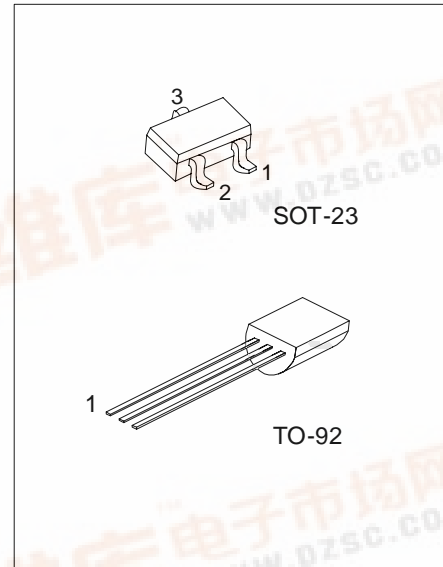
8550S

PNP SILICON TRANSISTOR

LOW VOLTAGE HIGH CURRENT
SMALL SIGNAL PNP
TRANSISTOR

FEATURES

- *Collector current up to 700mA
- *Collector-Emitter voltage up to 20 V
- *Complimentary to 8550S



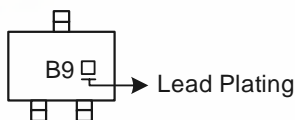
*Pb-free plating product number: 8550SL

ORDERING INFORMATION

Order Number		Package	Pin Assignment			Packing
Normal	Lead Free Plating		1	2	3	
8550S-x-AE3-R	8550SL-x-AE3-R	SOT-23	E	B	C	Tape Reel
8550S-x-T92-B	8550SL-x-T92-B	TO-92	E	C	B	Tape Box
8550S-x-T92-K	8550SL-x-T92-K	TO-92	E	C	B	Bulk

<p>8550SL-x-AE3-R</p>	<p>(1) B: Tape Box, K: Bulk, R: Tape Reel</p> <p>(2) AE3: SOT-23, T92: TO-92</p> <p>(3) x: refer to Classification of h_{FE2}</p> <p>(4) L: Lead Free Plating, Blank: Pb/Sn</p>
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MARKING (For SOT-23 Package)



8550S

PNP SILICON TRANSISTOR

■ ABSOLUTE MAXIMUM RATINGS (Ta = 25)

PARAMETER	SYMBOL	RATING	UNITS
Collector-Base Voltage	V _{CBO}	-30	V
Collector-Emitter Voltage	V _{CEO}	-20	V
Emitter-Base Voltage	V _{EBO}	-5	V
Collector Dissipation(Ta=25)	SOT-23	350	mW
	TO-92	1	W
Collector Current	I _c	-700	mA
Junction Temperature	T _J	+150	°C
Storage Temperature	T _{STG}	-40 ~ +150	°C

Note Absolute maximum ratings are those values beyond which the device could be permanently damaged. Absolute maximum ratings are stress ratings only and functional device operation is not implied.

■ ELECTRICAL CHARACTERISTICS (Ta= 25 , unless otherwise specified)

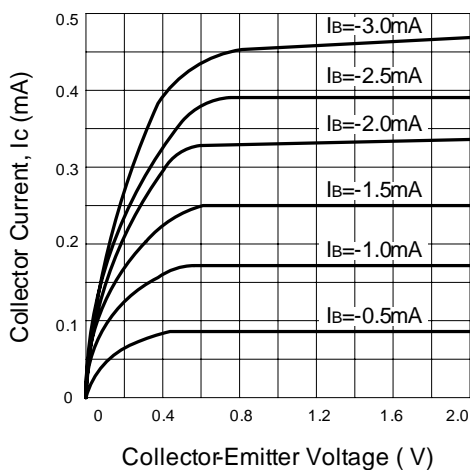
PARAMETER	SYMBOL	TEST CONDITIONS	MIN	TYP	MAX	UNIT
Collector-Base Breakdown Voltage	BV _{CBO}	I _c =-100μA, I _E =0	-30			V
Collector-Emitter Breakdown Voltage	BV _{CEO}	I _c =-1mA, I _B =0	-20			V
Emitter-Base Breakdown Voltage	BV _{EBO}	I _E =-100μA, I _c =0	-5			V
Collector Cut-off Current	I _{CBO}	V _{CB} =-30V, I _E =0			-1	uA
Emitter Cut-off Current	I _{EBO}	V _{EB} =-5V, I _c =0			-100	nA
DC Current Gain	h _{FE1}	V _{CE} =-1V, I _c =-1mA	100			
	h _{FE2}	V _{CE} =-1V, I _c =-150 mA	120		400	
	h _{FE3}	V _{CE} =-1V, I _c =-500mA	40			
Collector-Emitter Saturation Voltage	V _{CE(SAT)}	I _c =-500mA, I _B =-50mA			-0.5	V
Base-Emitter Saturation Voltage	V _{BE(SAT)}	I _c =-500mA, I _B =-50mA			-1.2	V
Base-Emitter Saturation Voltage	V _{BE}	V _{CE} =-1V, I _c =-10mA			-1.0	V
Current Gain Bandwidth Product	f _T	V _{CE} =-10V, I _c =-50mA	100			MHz
Output Capacitance	C _{ob}	V _{CB} =-10V, I _E =0, f=1MHz		9.0		pF

■ CLASSIFICATION OF h_{FE2}

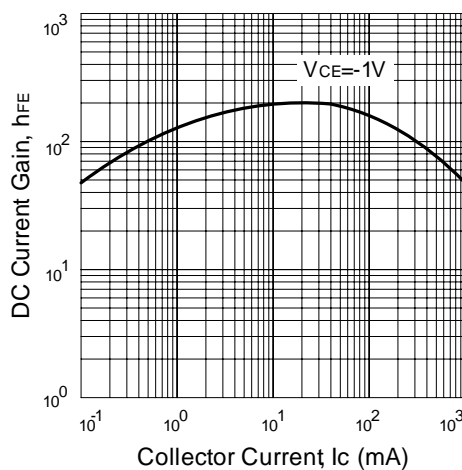
RANK	C	D	E
RANGE	120-200	160-300	280-400

TYPICAL CHARACTERISTICS

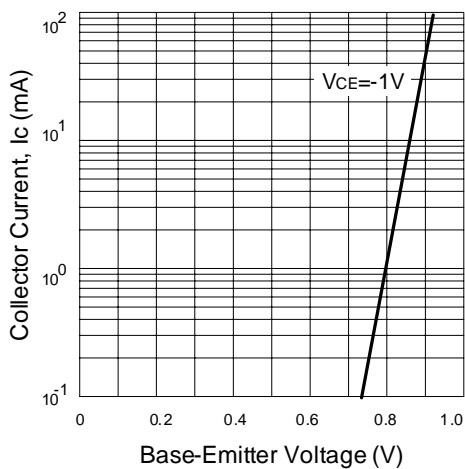
Static Characteristics



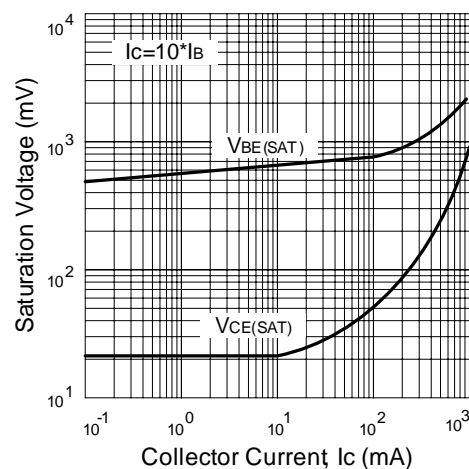
DC Current Gain



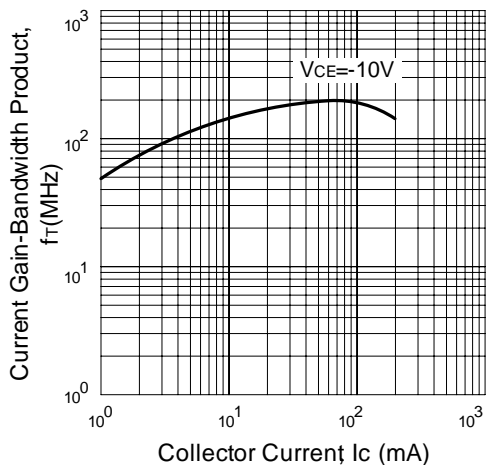
Base-Emitter on Voltage



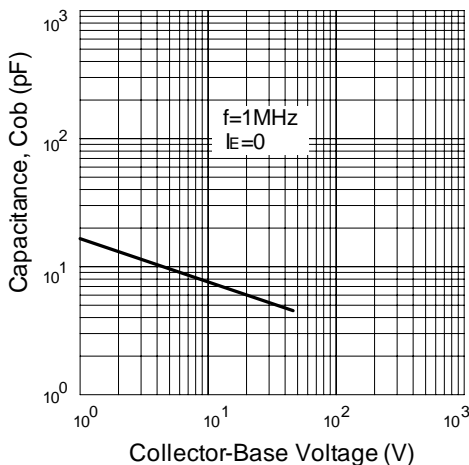
Saturation Voltage



Current Gain-Bandwidth Product



Collector Output Capacitance



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